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Early Photon Detector R&D for Particle Physics and Beyond

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Discovery, accelerated

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Scope of this talk

- Discuss photodetector R&D at the device level
- VUV-SiPMs for nEXO and other particle physics experiments
- Work being done at TRIUMF, impact on experiments and technology transfer
- Work loosely grouped into TRL categories of 'emerging,' 'prototyping,' 'integration'

Silicon photomultipliers

- **E** Array of SPAD pixels
- Compact, robust, insensitive to magnetic fields, fast timing
- Easier to produce large photosensitive area than using PMTs
- Cons: dark count, crosstalk

emerging

VUV -SiPMs for particle physics

- \blacksquare **nEXO will use 4.5m² of** SiPMs to detect LXe scintillation light
- FBK and Hamamatsu (candidate vendors for nEXO) have developed VUV SiPMs for nEXO – this was needed for the experiment to work
- Development is ongoing and driven by the needs of experiments (eg tsv's for nEXO)
- **30m² for Darkside-20K,** Argo may use 200m²(!)

emerging

Characterization at TRIUMF

PDE_[%]

- First step to incorporating devices in an experiment is characterizing the basic parameters - PDE, DCR, afterpulsing
- Devices meet fundamental nEXO requirements – shows feasibility
- Also necessary to understand the challenges of integrating devices into a detector
- Developing protocols for mass testing

Understanding pathologies - external crosstalk

- SPAD avalanches emit photons
- SiPMs triggering each other leads to 'external crosstalk' and degrades energy resolution

Diagram of eXT occurring between two SiPMs. **A** designates charge avalanche

- Not good! Effect needs to be well quantified
- Can be empirically studied using LolX detector at McGill

Secondary emission

- **EXPERITE MEASUREM IN STATE IS A PROPERTY MEASUREM** of photons emitted during avalanche using MIEL setup at TRIUMF
- **EXO candidate devices measured for** direct input to detector simulations
- **Work ongoing to measure emission** from individual SPADs in a digital SiPM, aiding understanding of emission mechanisms
- Can then contribute to future device design – enabling future technological improvements through study of a specific detector pathology

Modelling PDE

- **Predicting crosstalk** now requires understanding device response at secondary emission wavelengths
- Modelling PDE lets us extrapolate to wavelengths we can't measure
- Also provides details on device structure

 $PDE = FF \cdot T(\lambda, \theta_1, t_{oxide}) \cdot \big(W_p(\lambda, dp^*, X_{PN})p_e(V) + W_n(\lambda, X_{PN}, dw^*)p_h(V) \big)$

Modelling optics

- **Optical transmission** into device is not simple!
- **Passivation layer** thickness, interference, shape of the device microstructure play a role
- Angular dependence is important for detector simulations

Interference oscillations in FBK device

Technology transfer – device modelling for design of a unity-PDE SPAD emerging

- Several avenues for improving SPAD efficiency – antireflection coatings can be produced with close to 0 reflectivity at certain wavelengths
- Controlling region thicknesses and electric field profile can also maximize PDE while keeping DCR low
- **Probably possible to produce a** 100% PDE silicon SPAD with the right design choices

High efficiency SPADs for quantum applications emerging

- **Quantum computing requires very high PDE and single-photon** resolution at high photon numbers -> currently need SNSPDs to do this
- **An ultra-high PDE SPAD would enable quantum computing at** high(er) temperatures (the Xanadu quantum computer currently only uses dilution fridge temps for the single photon detectors)
- Could also permit high rate QKD systems!!

Quantum yield

■ 'Quantum yield' is the number of carrier pairs produced by a single photon absorption – increases above 1 at high energies

Normalized event

- Understanding needed for
detector event reconstruction detector event reconstruction – but applicable to a range of deep UV detection applications
- **Also applicable for detection** of dark photons and design of VUV photodetectors

integration

Mass testing

- Operation of >40k SiPMs over 10 years requires in-depth understanding of reliability and pathologies
- Development underway to produce fast and effective diagnostics
- Much of this will be transferable
	- **Extraction of device parameters from IV** rather than waveform-level measurements
	- Determining whether high-temperature performance can reliably infer lowtemperature performance
- Darkside is using a 'goodness of fit' parameter to a reference IV – we hope to be able to improve on this

Figures from DarkSide testing – thanks Giacomo \odot 13

Digital SiPMs emerging

- Individual SPAD readout and control
- Potential for spatial resolution and deactivation of faulty/high DCR SPADs
- Could be used to mitigate radiation damage

- nEXO and other particle physics experiments have motivated a significant R&D push in SiPM technology, in industrial and academic settings
- This enables better physics detectors now and better technology available for designing future detectors
- It also results in better understanding of SPAD operation and feeds back in to improved photodetectors for a wide range of applications

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Thank you **Merci**

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MIEL

Cryogenically Cooled X-Y Stage with SiPM **Mounted**

VERA

Vacuum Efficiency, Reflectivity, and Absorption

- Vacuum chamber to allow transmission of VUV light
- Deuterium light source with emission from VUV to NIR (140-830nm), wavelength controlled with vacuum monochromator
- Control of various parameters: Temperature, light source, optical angle of incidence
- Digitizer used for waveform-level measurements allows pulse counting and determination of photon detection rates

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